



SHEET 1 OF 13

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Substitute for form 1449/PTO)				ATTY. DOCKET NO. 061282-0234		SERIAL NO. 10/574,863	
				APPLICANT Yuichiro SASAKI, et al.			
				FILING DATE April 06, 2006		GROUP 2823	
U.S. PATENT DOCUMENTS							
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